ABSTRACT OF THE DISCLOSURE

A semiconductor device is improved in adhesion between: at least a contact portion of its tantalum-base metal serving as a barrier metal film; and, its copper buried wiring brought into contact with the contact portion to prevent the copper buried wiring from peeling off, and is therefore improved in reliability. Formed in a trench designed for a buried wiring of an interlayer insulation film are: a tantalum film having a film thickness of from 200 to 500 angstroms; and, a copper buried wiring having a film thickness of from 1.1 to 1.55 μm. This copper buried wiring is formed by stacking together a copper thin film having a film thickness of from 0.08 to 0.12 μm and a copper thick film having a film thickness of from 1.0 to 1.5 μm. Further formed between the tantalum film and the copper buried wiring is an amorphous metal film having a thickness of approximately angstroms. Still further formed between the tantalum film and each of a surface protection film and an interlayer insulation film is a tantalum oxide film having a film thickness of approximately several angstroms.